

December 1992

## CMOS BCD-To-Decimal Decoder

**Features**

- High Voltage Type (20V Rating)
- BCD-to-Decimal Decoding or Binary-to-Octal Decoding
- High Decoded Output Drive Capability
- “Positive Logic” Inputs and Outputs - Decoded Outputs Go High On Selection
- Medium-Speed Operation
  - t<sub>PHL</sub>, t<sub>PLH</sub> = 80ns (typ) at VDD = 10V
- Standardized Symmetrical Output Characteristics
- 100% Tested For Quiescent Current at 20V
- Maximum Input Current of 1 $\mu$ A at 18V Over Full Package-Temperature Range;
  - 100nA at 18V and +25°C
- Noise Margin (Over Full Package Temperature Range):
  - 1V at VDD = 5V
  - 2V at VDD = 10V
  - 2.5V at VDD = 15V
- 5V, 10V and 15V Parametric Ratings
- Meets All Requirements of JEDEC Tentative Standard No. 13B, “Standard Specifications for Description of ‘B’ Series CMOS Devices”

**Applications**

- Code Conversion
- Indication-Tube Decoder
- Address Decoding - Memory Selection Control

**Description**

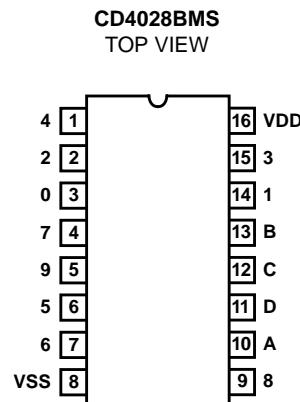
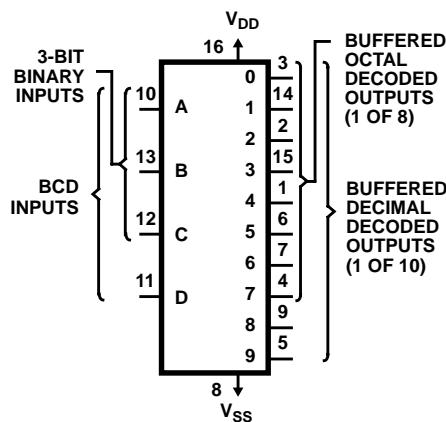
CD4028BMS types are BCD-to-decimal or binary-to-octal decoders consisting of buffering on all 4 inputs, decoding logic gates, and 10 output buffers. A BCD code applied to the four inputs, A to D, results in a high level at the selected one of 10 decimal decoded outputs. Similarly, a 3-bit binary code applied to inputs A through C is decoded in octal code at output 0 to 7 if D = “0”. High drive capability is provided at all outputs to enhance dc and dynamic performance in high fan-out applications.

The CD4028BMS is supplied in these 16-lead outline packages:

Braze Seal DIP H4S

Frit Seal DIP H1E

Ceramic Flatpack H3X

**Pinout****Functional Diagram**

# Specifications CD4028BMS

## Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) .....	-0.5V to +20V (Voltage Referenced to VSS Terminals)
Input Voltage Range, All Inputs .....	-0.5V to VDD +0.5V
DC Input Current, Any One Input .....	±10mA
Operating Temperature Range.....	-55°C to +125°C Package Types D, F, K, H
Storage Temperature Range (TSTG).....	-65°C to +150°C
Lead Temperature (During Soldering) .....	+265°C At Distance 1/16 ± 1/32 Inch (1.59mm ± 0.79mm) from case for 10s Maximum

## Reliability Information

Thermal Resistance .....	$\theta_{ja}$	$\theta_{jc}$
Ceramic DIP and FRIT Package .....	80°C/W	20°C/W
Flatpack Package .....	70°C/W	20°C/W
Maximum Package Power Dissipation (PD) at +125°C		
For TA = -55°C to +100°C (Package Type D, F, K) .....	500mW	
For TA = +100°C to +125°C (Package Type D, F, K) .....	Derate Linearity at 12mW/°C to 200mW	
Device Dissipation per Output Transistor .....	100mW	
For TA = Full Package Temperature Range (All Package Types)		
Junction Temperature .....		+175°C

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS	
					MIN	MAX		
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1	+25°C	-	10	µA	
			2	+125°C	-	1000	µA	
		VDD = 18V, VIN = VDD or GND	3	-55°C	-	10	µA	
Input Leakage Current	IIL	VIN = VDD or GND	VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load	1, 2, 3	+25°C, +125°C, -55°C	-	50	mV	
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)	1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V	
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1	+25°C	0.53	-	mA	
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1	+25°C	1.4	-	mA	
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1	+25°C	3.5	-	mA	
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1	+25°C	-	-0.53	mA	
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1	+25°C	-	-1.8	mA	
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1	+25°C	-	-1.4	mA	
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1	+25°C	-	-3.5	mA	
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1	+25°C	-2.8	-0.7	V	
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10µA	1	+25°C	0.7	2.8	V	
Functional	F	VDD = 2.8V, VIN = VDD or GND	7	+25°C	VOH > VDD/2	VOL < VDD/2	V	
		VDD = 20V, VIN = VDD or GND	7	+25°C				
		VDD = 18V, VIN = VDD or GND	8A	+125°C				
		VDD = 3V, VIN = VDD or GND	8B	-55°C				
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5V, VOL < 0.5V	1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V	
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5V, VOL < 0.5V	1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V	
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13.5V, VOL < 1.5V	1, 2, 3	+25°C, +125°C, -55°C	-	4	V	
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13.5V, VOL < 1.5V	1, 2, 3	+25°C, +125°C, -55°C	11	-	V	

NOTES: 1. All voltages referenced to device GND, 100% testing being implemented.

2. Go/No Go test with limits applied to inputs.

3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

# Specifications CD4028BMS

**TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS**

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay	TPHL TPLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	350	ns
			10, 11	+125°C, -55°C	-	473	ns
Transition Time	TTHL TTLH	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
			10, 11	+125°C, -55°C	-	270	ns

NOTES:

- CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 55°C and +125°C limits guaranteed, 100% testing being implemented.

**TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	5	µA
				+125°C	-	150	µA
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	µA
				+125°C	-	300	µA
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	10	µA
				+125°C	-	600	µA
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.4V	1, 2	+125°C	0.36	-	mA
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	7	-	V

## Specifications CD4028BMS

**TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay	TPHL TPLH	VDD = 10V	1, 2, 3	+25°C	-	160	ns
		VDD = 15V	1, 2, 3	+25°C	-	120	ns
Transition Time	TTHL TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN		1, 2	+25°C	-	7.5	pF

NOTES:

1. All voltages referenced to device GND.
2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

**TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	25	µA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10µA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10µA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10µA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH > VDD/2	VOL < VDD/2	V
		VDD = 3V, VIN = VDD or GND					
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

3. See Table 2 for +25°C limit.

4. Read and Record

**TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C**

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-2	IDD	± 1.0µA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

**TABLE 6. APPLICABLE SUBGROUPS**

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	
Interim Test 3 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
PDA (Note 1)	100% 5004	1, 7, 9, Deltas	

## Specifications CD4028BMS

**TABLE 6. APPLICABLE SUBGROUPS (Continued)**

CONFORMANCE GROUP		MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11	
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11	
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11
	Subgroup B-6	Sample 5005	1, 7, 9	
Group D		Sample 5005	1, 2, 3, 8A, 8B, 9	Subgroups 1, 2 3

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

**TABLE 7. TOTAL DOSE IRRADIATION**

CONFORMANCE GROUPS	MIL-STD-883 METHOD	TEST		READ AND RECORD	
		PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4

**TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS**

FUNCTION	OPEN	GROUND	VDD	9V $\pm$ 0.5V	OSCILLATOR	
					50kHz	25kHz
Static Burn-In 1 Note 1	1 - 7, 9, 14, 15	8, 10 - 13	16			
Static Burn-In 2 Note 1	1 - 7, 9, 14, 15	8	10 - 13, 16			
Dynamic Burn-In Note 1	-	8	16	1 - 7, 9, 14, 15	10, 12, 13	11
Irradiation Note 2	1 - 7, 9, 14, 15	8	10 - 13, 16			

NOTE:

1. Each pin except VDD and GND will have a series resistor of  $10K \pm 5\%$ ,  $VDD = 18V \pm 0.5V$
2. Each pin except VDD and GND will have a series resistor of  $47K \pm 5\%$ ; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures,  $VDD = 10V \pm 0.5V$

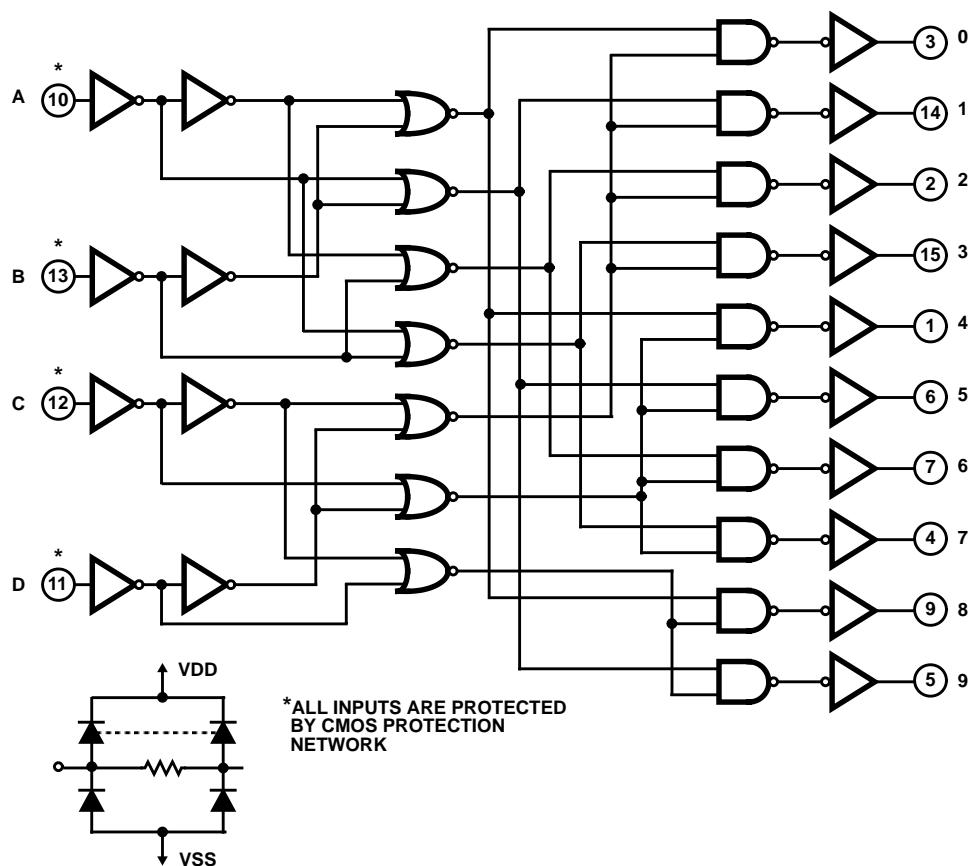
**Logic Diagram**

TABLE 1. TRUTH TABLE

D	C	B	A	0	1	2	3	4	5	6	7	8	9
0	0	0	0	1	0	0	0	0	0	0	0	0	0
0	0	0	1	0	1	0	0	0	0	0	0	0	0
0	0	1	0	0	0	1	0	0	0	0	0	0	0
0	0	1	1	0	0	0	1	0	0	0	0	0	0
0	1	0	0	0	0	0	0	1	0	0	0	0	0
0	1	0	1	0	0	0	0	0	1	0	0	0	0
0	1	1	0	0	0	0	0	0	0	1	0	0	0
0	1	1	1	0	0	0	0	0	0	0	1	0	0
1	0	0	0	0	0	0	0	0	0	0	0	1	0
1	0	0	1	0	0	0	0	0	0	0	0	0	1
1	0	1	0	0	0	0	0	0	0	0	0	0	0
1	0	1	1	0	0	0	0	0	0	0	0	0	0
1	1	0	0	0	0	0	0	0	0	0	0	0	0
1	1	0	1	0	0	0	0	0	0	0	0	0	0
1	1	1	0	0	0	0	0	0	0	0	0	0	0
1	1	1	1	1	0	0	0	0	0	0	0	0	0

1 = HIGH LEVEL

0 = LOW LEVEL

## Typical Performance Characteristics

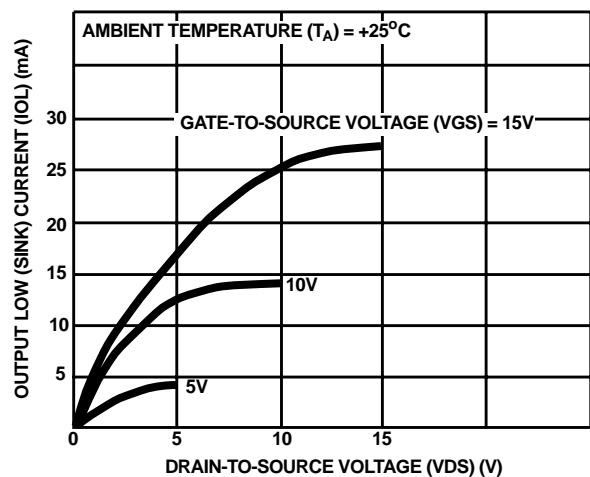


FIGURE 1. TYPICAL OUTPUT LOW (SINK) CURRENT CAPACITANCE

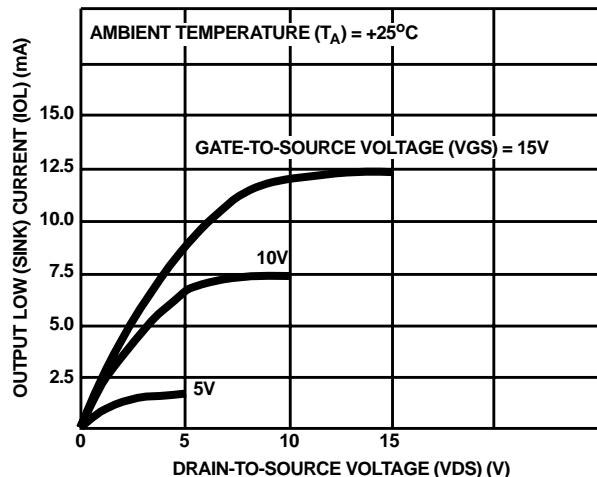


FIGURE 2. MINIMUM OUTPUT LOW (SINK) CURRENT CAPACITANCE

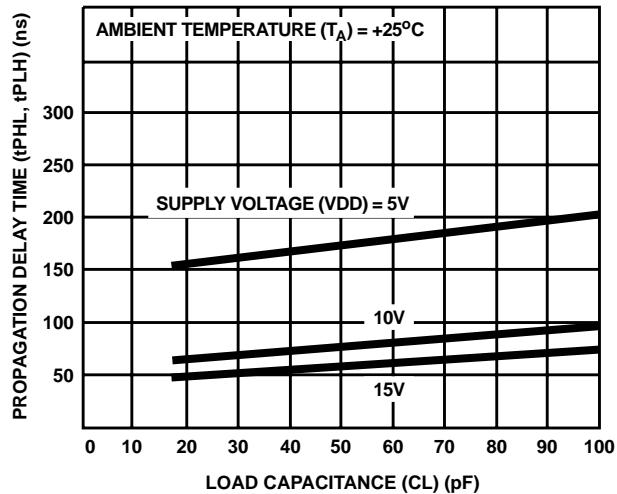


FIGURE 3. TYPICAL PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE

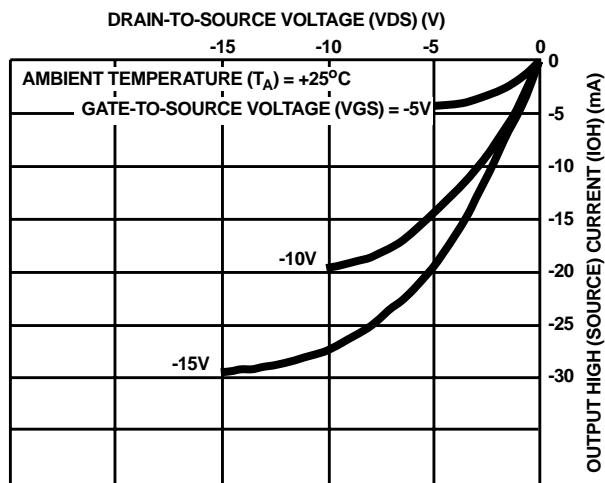


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

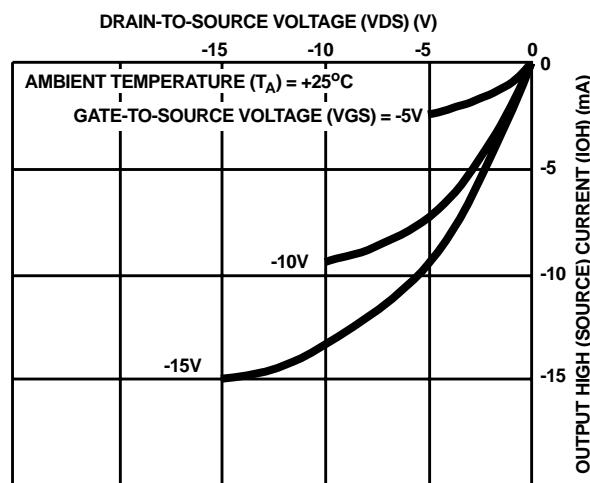


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

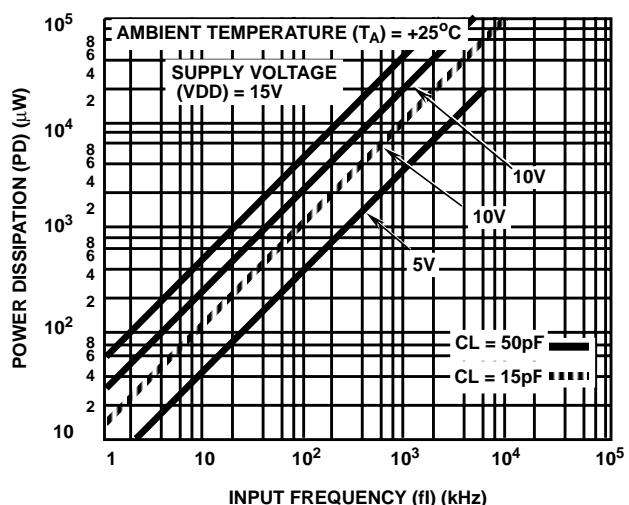


FIGURE 6. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF INPUT FREQUENCY

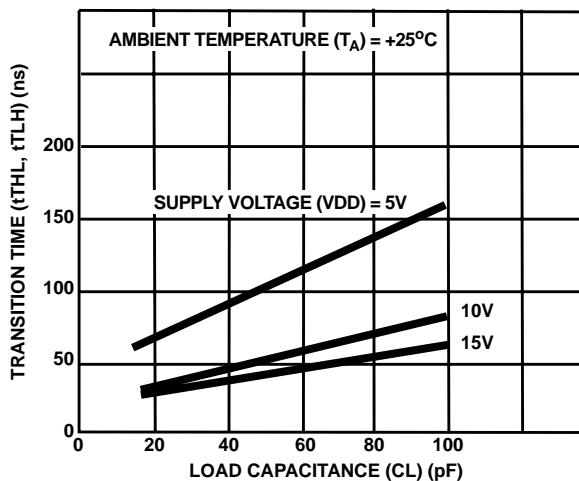
**Typical Performance Characteristics (Continued)**

FIGURE 7. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

**Typical Applications**

The circuit shown in Figure 8 converts any 4-bit code to a decimal or hexadecimal code. Table 2 shows a number of codes and the decimal or hexadecimal number in these codes which must be applied to the input terminals of the CD4028BMS to select a particular output. For example: in order to get a high on output number 8 the input must be either an 8 expressed in 4-bit Binary code, a 15 expressed in 4-Bit Gray code, or a 5 expressed in Excess-3 code.

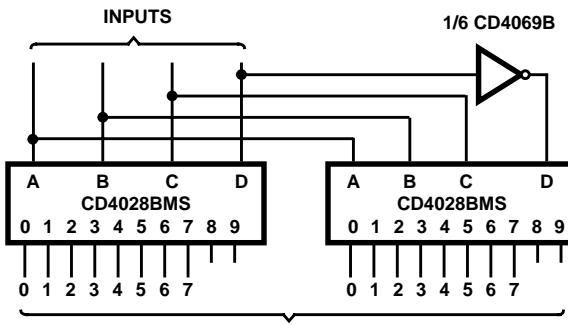


FIGURE 8. CODE CONVERSION CIRCUIT

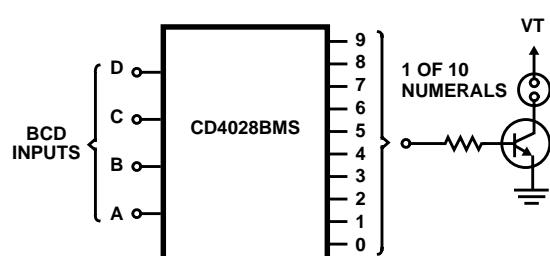
TABLE 2. CODE CONVERSION CHART

INPUTS				INPUT CODES						OUTPUT NUMBER															
				HEXA-DECIMAL		DECIMAL																			
D	C	B	A	4-BIT BINARY	4-BIT GRAY	EXCESS-3	EXCESS-3 GRAY	AIKEN	4-2-2-1	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
0	0	0	0	0	0			0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	
0	0	0	1	1	1			1	1	0	1	0	0	0	0	0	0	0	0	0	0	0	0	0	
0	0	1	0	2	3		0	2	2	0	0	1	0	0	0	0	0	0	0	0	0	0	0	0	
0	0	1	1	3	2	0	3	3		0	0	0	1	0	0	0	0	0	0	0	0	0	0	0	
0	1	0	0	4	7	1	4	4		0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	
0	1	0	1	5	6	2		3	0	0	0	0	0	1	0	0	0	0	0	0	0	0	0	0	
0	1	1	0	6	4	3	1		4	0	0	0	0	0	0	1	0	0	0	0	0	0	0	0	
0	1	1	1	7	5	4	2			0	0	0	0	0	0	0	1	0	0	0	0	0	0	0	
1	0	0	0	8	15	5				0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	
1	0	0	1	9	14	6				5	0	0	0	0	0	0	0	0	1	0	0	0	0	0	
1	0	1	0	10	12	7	9			6	0	0	0	0	0	0	0	0	0	1	0	0	0	0	

# CD4028BMS

TABLE 2. CODE CONVERSION CHART (Continued)

INPUTS				INPUT CODES				OUTPUT NUMBER																
				HEXA-DECIMAL		DECIMAL																		
D	C	B	A	4-BIT BINARY	4-BIT GRAY	EXCESS-3 EXCESS-3	GRAY AIKEN	4-2-2-1	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
1	0	1	1	11	13	8	5		0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	
1	1	0	0	12	8	9	5	6	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	
1	1	0	1	13	9		6	7	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
1	1	1	0	14	11		8	8	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1	0
1	1	1	1	15	10		7	9	9	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1



\*(TRADEMARK) BURROUGHS CORP.

### TUBE REQUIREMENTS

TYPE	VT(Vdc)	NUMERAL mA/
BURROUGHS	B4081	170
	B4336/718	170
	B4032	170
	B4021	120
TRANSISTOR CHARACTERISTICS		
Leakage with transistor cutoff $\leq 0.05\text{mA}$		
$V(\text{BR})\text{CEO} \geq 70\text{V}$		

FIGURE 9. NEON READOUT (NIXIE TUBE\*) DISPLAY APPLICATION

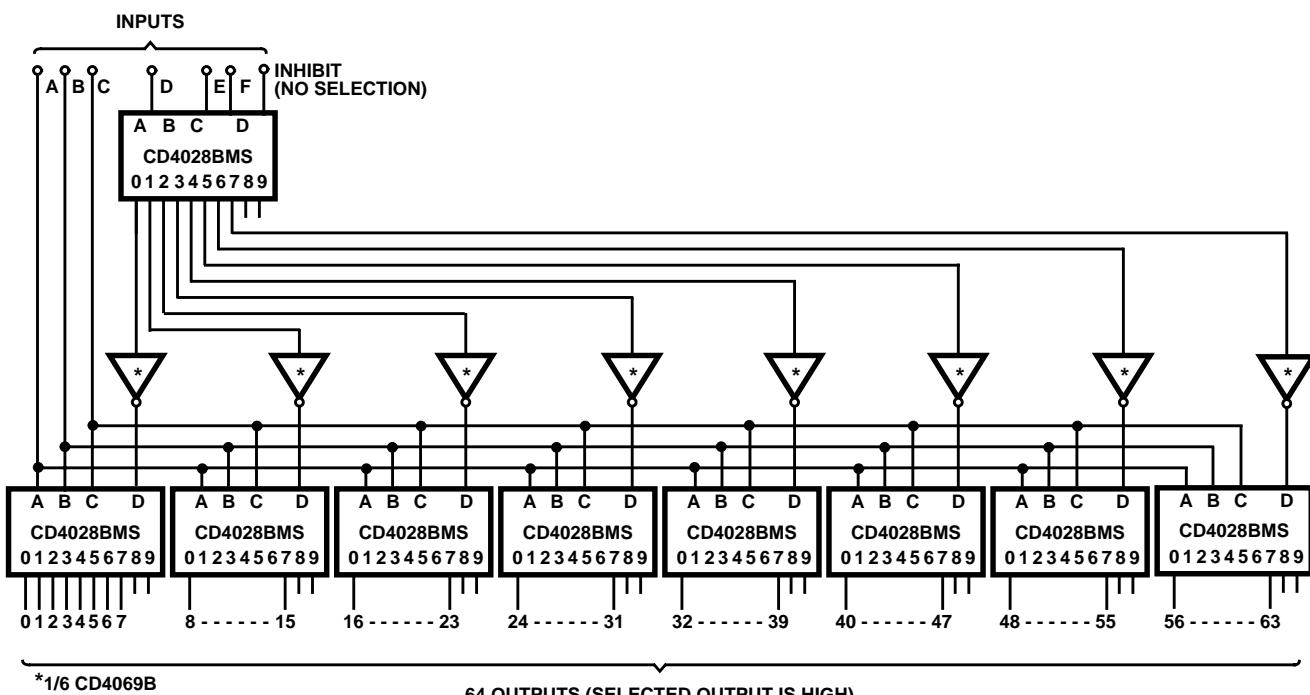
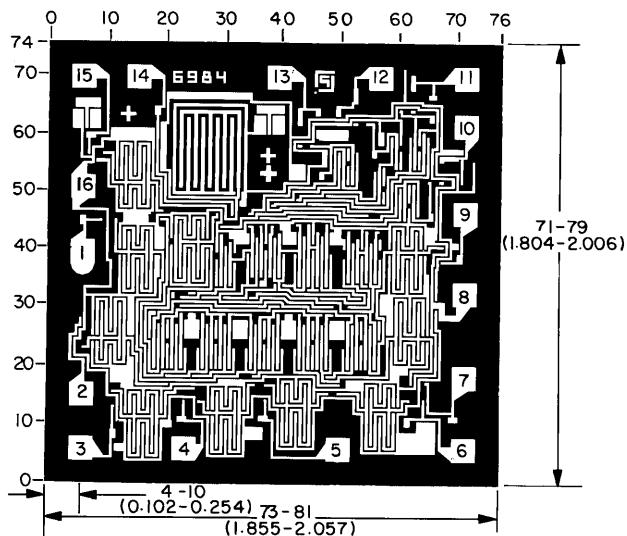


FIGURE 10. 6-BIT BINARY TO 1-OF-64 ADDRESS DECODER

**Chip Dimensions and Pad Layout**

Dimensions in parentheses are in millimeters  
and are derived from the basic inch dimensions  
as indicated. Grid graduations are in mils ( $10^{-3}$  inch)

**METALLIZATION:** Thickness:  $11\text{k}\text{\AA}$  –  $14\text{k}\text{\AA}$ , AL.

**PASSIVATION:**  $10.4\text{k}\text{\AA}$  -  $15.6\text{k}\text{\AA}$ , Silane

**BOND PADS:** 0.004 inches X 0.004 inches MIN

**DIE THICKNESS:** 0.0198 inches - 0.0218 inches

All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site <http://www.intersil.com>

**Sales Office Headquarters****NORTH AMERICA**

Intersil Corporation  
P. O. Box 883, Mail Stop 53-204  
Melbourne, FL 32902  
TEL: (321) 724-7000  
FAX: (321) 724-7240

**EUROPE**

Intersil SA  
Mercure Center  
100, Rue de la Fusée  
1130 Brussels, Belgium  
TEL: (32) 2.724.2111  
FAX: (32) 2.724.22.05

**ASIA**

Intersil (Taiwan) Ltd.  
Taiwan Limited  
7F-6, No. 101 Fu Hsing North Road  
Taipei, Taiwan  
Republic of China  
TEL: (886) 2 2716 9310  
FAX: (886) 2 2715 3029